

-30V P-Channel Enhancement Mode MOSFET

DESCRIPTION

The STP3401A is the P-Channel logic enhancement mode power field effect transistor is produced using high cell density. advanced trench technology to provide excellent $R_{DS(ON)}$. low gate charge and operation gate as 2.5V.

This device is suitable for use as a load switch or other general applications.

STP3401AS-TRG ROHS Compliant This is Halogen Free

FEATURE

- ◆ -30V/-4.3A, $R_{DS(ON)} = 50m\Omega (typ.) @ V_{GS} = -10V$
- ◆ -30V/-3.5A, $R_{DS(ON)} = 58m\Omega (typ.) @ V_{GS} = -4.5V$
- ◆ -30V/-2.5A, $R_{DS(ON)} = 73m\Omega (typ.) @ V_{GS} = -2.5V$
- ◆ Super high density cell design for extremely low $R_{DS(ON)}$
- ◆ Exceptional on-resistance and Maximum DC current capability

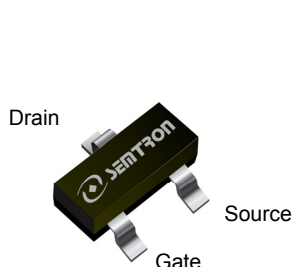
APPLICATIONS

- ◆ High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- ◆ DC/DC Converter
- ◆ Load Switch

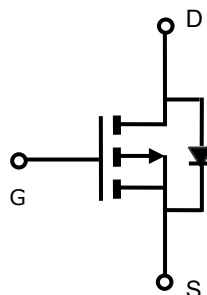


P-Channel Enhancement Mode MOSFET

PIN CONFIGURATION



SOT-23
Top View



PART NUMBER INFORMATION

ST P 3401A S - TR G
 a b c d e f

a : Company name.
 b : Channel type.
 c : Product Serial number.
 d : Package Code
 e : Handling Code
 f : Lead Plating Code
 G : Lead-free product.
This product is Halogen Free

ORDERING INFORMATION

Part Number	Package Code	Handling Code	Shipping
STP3401AS-TRG	S : SOT-23	TR : Tape&Reel	3K/Reel

※ Year Code : 0 ~ 9, 2010 : 0

※ Week Code : A(1~2) ~ Z(53~54)

※ SOT-23 : Only available in tape and reel packaging.

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ Unless otherwise noted)

Symbol	Parameter		Typical	Unit
V _{DSS}	Drain-Source Voltage		-30	V
V _{GSS}	Gate-Source Voltage		±12	V
I _D	Continuous Drain Current (T _C =25°C) ^A	V _{GS} =-12V	-4.3	A
	Continuous Drain Current (T _C =70°C) ^A		-3.8	A
I _{DM}	Pulsed Drain Current ^B		-20	A
P _D	Power Dissipation	T _A =25°C	1.25	W
		T _A =70°C	0.8	
T _J	Operation Junction Temperature		-55 to150	°C
T _{STG}	Storage Temperature Range		-55 to150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

THERMAL DATA

Symbol	Parameter		Typ	Max	Unit
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient ^A	Steady-State	-	120	$^\circ\text{C}/\text{W}$
$R_{\theta JL}$	Thermal Resistance Junction to Lead ^A	Steady-State	-	80	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS($T_J = 25^\circ\text{C}$ Unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Parameters						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-30			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.6		-1.0	V
I_{GSS}	Gate Leakage Current	$V_{DS}=0V, V_{GS}=\pm 12V$			± 100	nA
I_{DSS}	Zero Gate Voltage, Drain-Source Leakage Current	$V_{DS}=-24V, V_{GS}=0V$ $T_J=25^\circ\text{C}$			-1	μA
		$V_{DS}=-24V, V_{GS}=0V$ $T_J=55^\circ\text{C}$			-5	
$R_{DS(ON)}$	Drain-source On-Resistance ^B	$V_{GS}=-10V, I_D=-4.3A$		50	56	m Ω
		$V_{GS}=-4.5V, I_D=-3.5A$		58	65	
		$V_{GS}=-2.5V, I_D=-2.5A$		73	80	
G_{fs}	Forward Transconductance	$V_{DS}=-5V, I_D=-4.0A$		10		S
Source-Drain Diode						
V_{SD}	Diode Forward Voltage	$I_S=-1.0A, V_{GS}=0V$		-0.7	-1.0	V
I_S	Continuous Source Current ^{AD}				-5.6	A
Dynamic Parameters						
$Q_g (-4.5V)$	Total Gate Charge	$V_{DS}=-20V$		6.8		nC
Q_{gs}	Gate-Source Charge	$V_{GS}=-4.5V$		3.0		
Q_{gd}	Gate-Drain Charge	$I_D=-4.0A$		3.3		
C_{iss}	Input Capacitance	$V_{DS}=-12V$		681		pF
C_{oss}	Output Capacitance	$V_{GS}=0V$		290		
C_{rss}	Reverse Transfer Capacitance	$f=1\text{MHz}$		112		
$t_{d(on)}$	Turn-On Time	$V_{DD}=-12V$		10		nS
t_r		$I_D=-4A$		16		
$t_{d(off)}$	Turn-Off Time	$V_{GEN}=-10V$		24		
t_f		$R_G=3.3\Omega$		22		

Note:

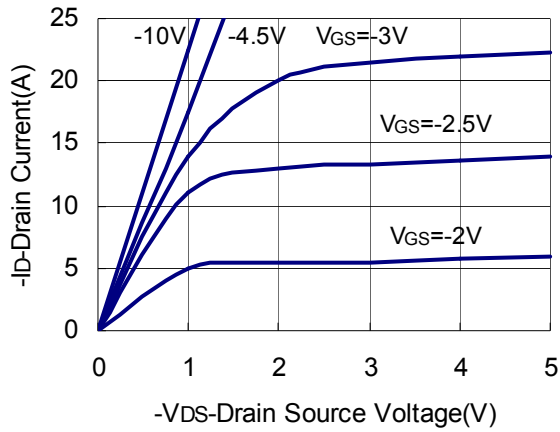
- The value of $R_{\theta JA}$ is measured with the device mounted on 1in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$.
- The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- The EAS data shows Max. rating . The test condition is $V_{DD}=-25V, V_{GS}=-10V, L=0.1mH$.
- The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

The products and product specifications contained herein are subject to change without notice to improve performance characteristics. Consult us, or our representatives before use, to confirm that the information in this datasheet is up to date

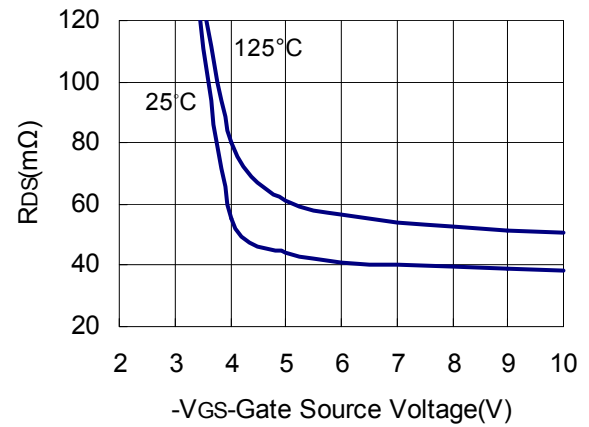
We assume no responsibility for any infringement of patents, patent rights, or other rights arising from the use of any information and circuitry in this datasheet.

TYPICAL CHARACTERISTICS (25°C Unless Note)

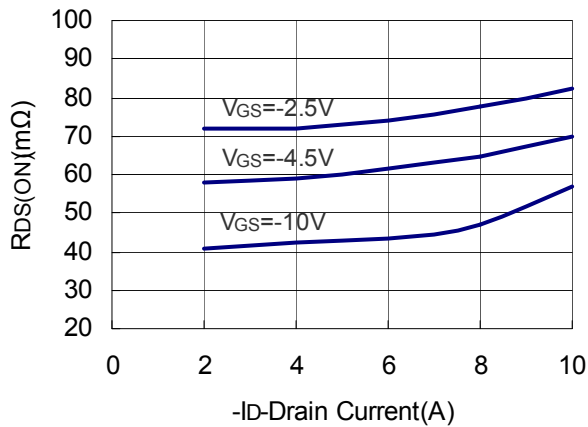
Output Characteristics



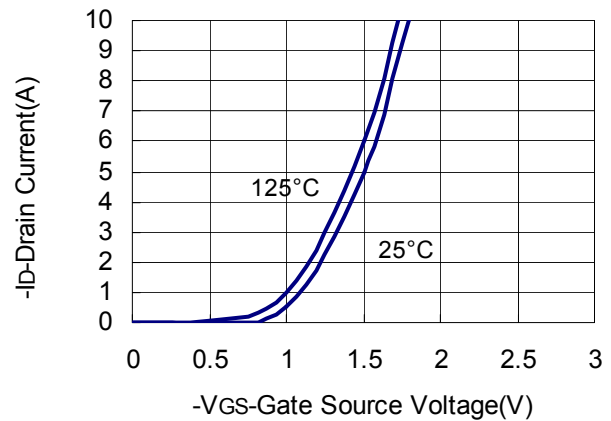
Drain-Source On Resistance



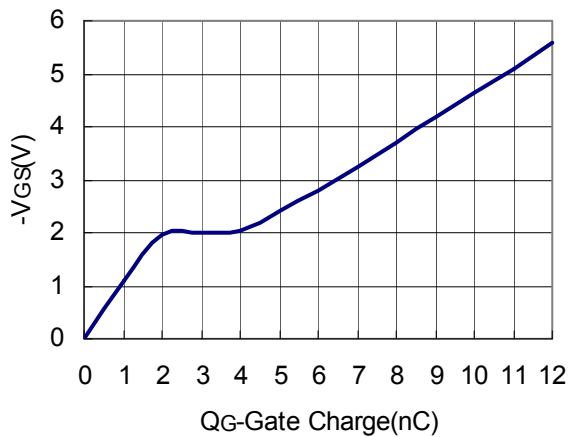
Drain Source On Resistance



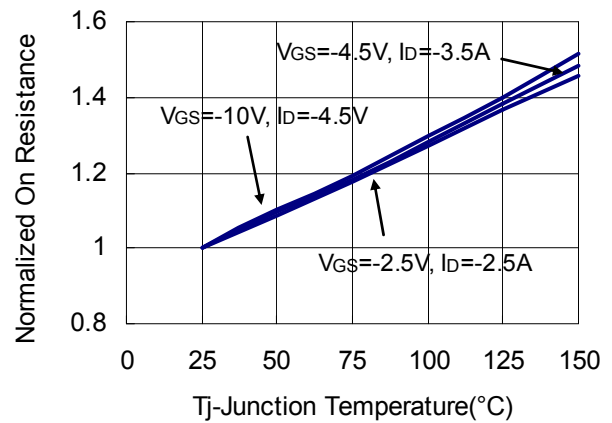
Transfer Characteristics



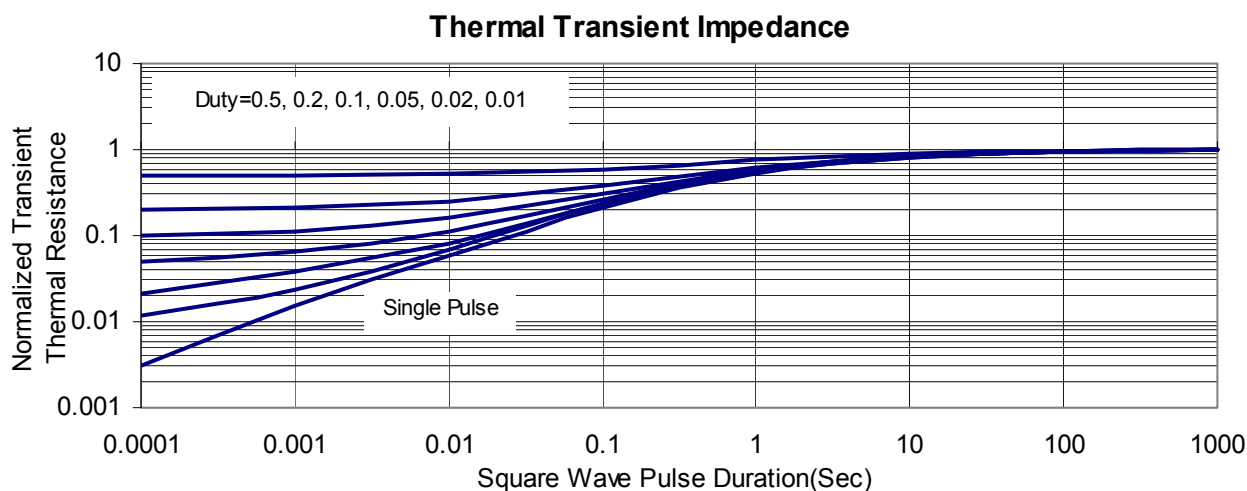
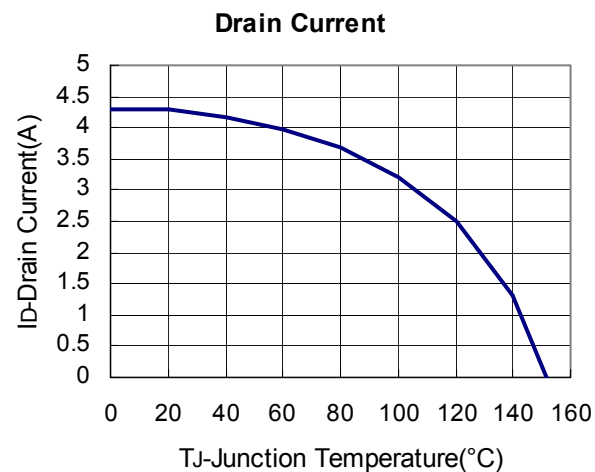
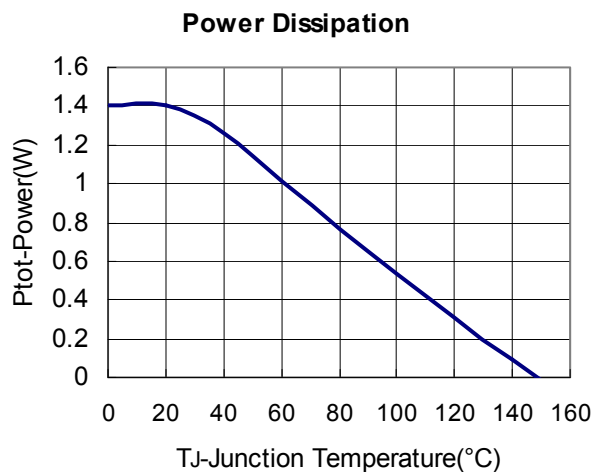
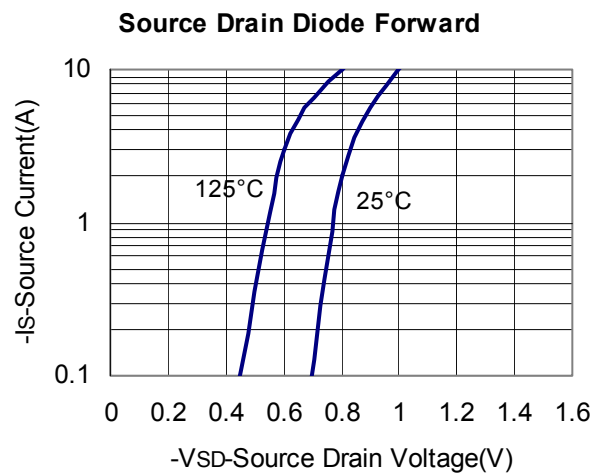
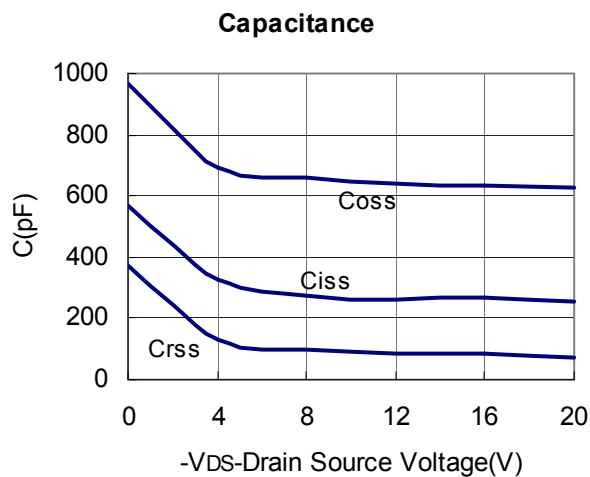
Gate Charge



Drain Source Resistance



TYPICAL CHARACTERISTICS (25°C Unless Note)



■ SOT-23 PACKAGE DIMENSIONS

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L1	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

